

## 8K x 8 16K x 8 CMOS DUAL-PORT STATIC RAM MODULE (SLAVE)

IDT7M144S

#### **FEATURES:**

- High-density 64K/128K CMOS SLAVE Dual-Port static RAM modules
- 16K x 8 (IDT7M145) or 8K x 8 (IDT7M144) option
- Easily expands data bus width to 16-or-more-bits when used with MASTER IDT7M134 or IDT7M135 modules
- · Fully asynchronous read/write operation from either port
- · Fast access time
  - commercial: 30ns (max.)
- military: 40ns (max.)
- Low-power consumption
- BUSY output flags
- · Dual Vcc and GND pins for maximum noise immunity
- Inputs and outputs directly TTL-compatible
- Single 5V (±10%) power supply

#### **DESCRIPTION:**

The IDT7M144/IDT7M145 are 64K/128K high-speed CEMOS™ SLAVE Dual-Port static RAM modules constructed on a multi-layered, co-fired, ceramic substrate using four IDT7142 2K x 8 SLAVE dual-port static RAMs (IDT7M144) or eight IDT7142 SLAVE dual-port static RAMs (IDT7M145) in leadless chip carriers. Dual-port function is achieved by utilization of the two on-board IDT54/IDT74FCT138 decoder circuits that interpret the higher order addresses AL11-13 and AR11-13 to select one of the

eight 2K x 8 dual-port static RAMs. (On IDT7M144 8K x 8 option, the AL13 and AR13 need to be externally grounded and the selection becomes one of the four 2K x 8 dual-port static RAMs).

The IDT7M144/IDT7M145 are designed as "SLAVE" dual-port static RAM modules to be used together with the IDT7M135/IDT7M135 "MASTER" dual-port RAM modules in 16-or-more-bit systems, whereas the IDT7M134/IDT7M135 are designed to be used as stand-alone 8-bit dual-port static RAM modules. Using the IDT MASTER/SLAVE dual-port static RAM module approach in 16-or-more-bit memory system applications results in full speed operation without the need for additional discrete logic.

Both SLAVE IDT7M144/IDT7M145 and MASTER IDT7M134/IDT7M135 modules provide two ports with separate control, address and I/O pins that permit independent asynchronous access for reads or writes to any location in the memory. The BUSY flags are provided for the situation when both ports simultaneously access the same memory location. BUSY is set at speeds that permit the processor to hold the operation and its respective address and data. The delayed port will have access when BUSY goes high (inactive). The BUSY pins are outputs on the MASTER and inputs on the SLAVE.

All military module semiconductor components are manufactured in compliance with the latest revision of MIL-STD-883 Class B, making them ideally suited for applications demanding the highest level of performance and reliability.

## PIN CONFIGURATION (3)

	_
GND 🗆	58 □ Vcc
<u>CS</u> ∟∐2	57 🗖 ĈŜR
	56 □ R/WR
NC ☐4	55 🗆 NC
BUSY (2)	54 BUSYR(2)
POSTE, 72	24 F 552 LV-1
ŌĒ∟∏6	53 □ ŌĒR
Aol 7	52 🗖 A0R
	25 H 204
A1L □ 8	51 🗆 A1R
A2L ☐ 9	50 🗖 A₂R
A3L 🔲 10	49 🗀 A3R
A4L 🗀 11	48 🗆 A4R
	47 ☐ A5R
A6L 🗍 13	46 🗌 A6R
A7L 🗌 14	45 🗆 A7R
A8L 🗌 15	44 🔲 A8R
A9L 🗆 16	43 🗀 A9R
	42 A10R
A11L 🗆 18	41 🗀 A <sub>11R</sub>
A12L 🗆 19	40 🗀 A <sub>12</sub> R
	33 H 2 12 / 10
A13L(1) 20	39 🗀 A <sub>13R</sub> (1)
I/O oL □ 21	38 🗆 I/Oor
	37 🗆 I/O18
I/O 2L 🗌 23	36 🔲 1/O2R
1/O 3L 24	35 🗌 I/O3R
1/O 4L 🗀 25	34 🔲 I/O4R
I/O 5L 🗌 26	33 🔲 I/O5R
I/O 6L □ 27	32 🔲 I/O6R
1/0 71 🗌 28	31 🗌 l/O78
GND 🗖 29	30 □ Vcc

2687 dwg 01

IN NAMES						
Left Port	Right Port	Names				
AOL-A13L	AOR-A13R	Address Input				
1/OoL-107L	I/OoR-I/O7R	Data Input/Output				
CSL	CSR	Chip Select				
R/WL	R/WR	Read/Write Enable				
ŌĒL	ŌĒR	Output Enable				
BUSYL	BUSYR	BUSY Input				
Vcc	Vcc	Power				
GND	GND	Ground				

#### NOTES:

DIN NAMES

- On 8K x 8 IDT7M144 option, Anal and Anar need to be externally connected to ground for proper operation.
- IDT7M134/IDT7M135 (MASTER): BUSY is open drain output and requires pull up resistor. IDT7M144/IDT7M145 (SLAVE): BUSY is input.
- For module dimensions, please refer to module drawing M12 in the packaging section.

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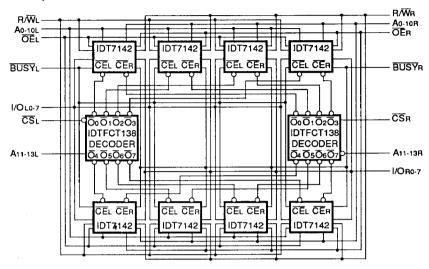
**MILITARY AND COMMERCIAL TEMPERATURE RANGES** 

DIP

TOP VIEW

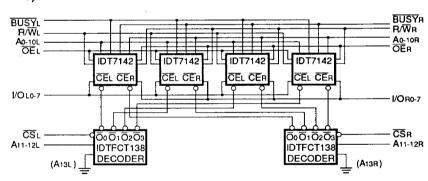
SEPTEMBER 1990

# FUNCTIONAL BLOCK DIAGRAMS IDT7M145 (16K x 8)



2687 dwg 02

#### IDT7M144 (8K x 8)



2687 dwg 03

(GROUND A13L AND A13R EXTERNALLY)

## DC ELECTRICAL CHARACTERISTICS

### OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE

(DC electricals for the IDT7M144/IDT7M145 SLAVE module are identical to the IDT7M134/IDT7M135 MASTER module. Reference the IDT7M134/IDT7M135 CMOS Dual-Port static RAM data sheet.)

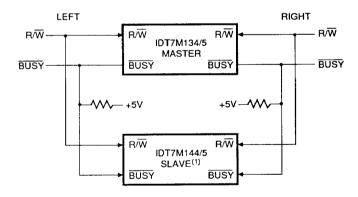
## AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE

(AC electricals for the IDT7M144/IDT7M145 SLAVE module are identical to the IDT7M134/IDT7M135 MASTER module except where noted below.)

				IDTM144S30 IDTM144S35 IDTM145S35 IDTM145S30 IDTM145S35						
Symbol	Parameter	(Com'l Min.	. Only) Max.	(Com'l Min.		1	Max.	Min.	Max.	Unit
twB	Write to BUSY	0		0		0		0		ns
twH	Write Hold After BUSY	20		20		20		20		ns

						IDTM144S60 IDTM144S70 IDTM145S60 IDTM145S70 (Mil. Only)						
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
twB	Write to BUSY	0		0	_	0	_	0	_	0		ns
twn	Write Hold After BUSY	20		20		20		20		20		ns

#### 16-BIT MASTER/SLAVE DUAL-PORT MEMORY SYSTEM



NOTE:

1. No arbitration in IDT7M144/IDT7M145 (SLAVE): BUSY in inhibits write in IDT7M144/IDT7M145.

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#### ORDERING INFORMATION

